

isc Silicon NPN Pow Transistor

2SC2383

DESCRIPTION

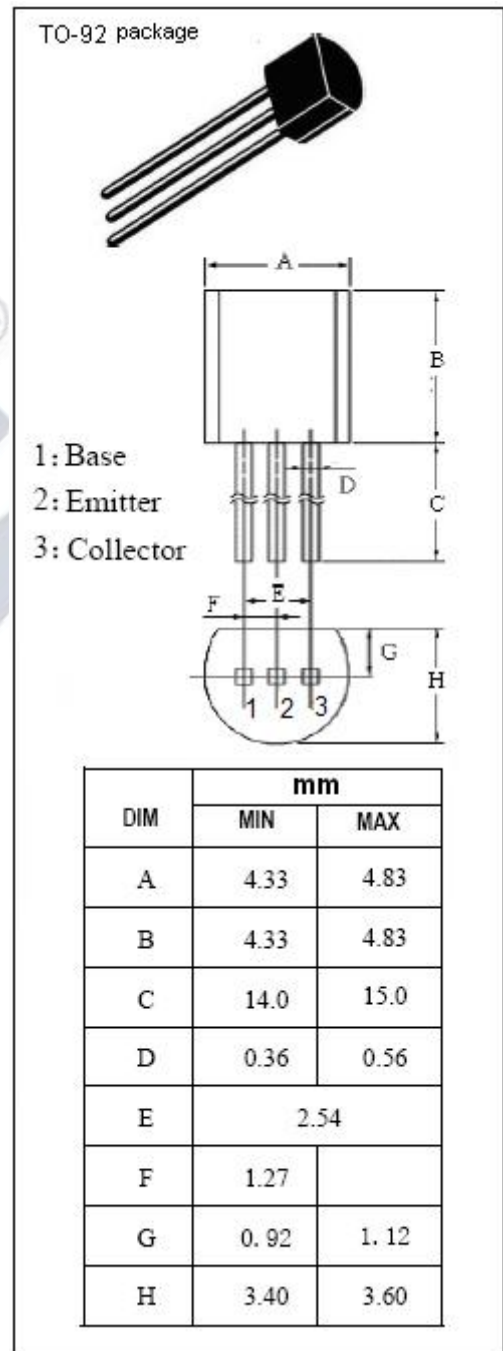
- High breakdown voltage
- Low output capacitance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Color TV class B sound output applications
- Color TV vert.deflection output applications

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CB0}	Collector-Base Voltage	160	V
V _{CEO}	Collector-Emitter Voltage	160	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current-Continuous	1	A
I _E	Emitter Current-Continuous	-1	A
P _C	Collector Power Dissipation @T _C =25°C	0.9	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



isc Silicon NPN Pow Transistor**2SC2383****ELECTRICAL CHARACTERISTICS** **$T_c=25^\circ\text{C}$ unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C= 500\text{mA}$; $I_B= 50\text{mA}$			1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C= 5\text{mA}$; $V_{CE}= 5\text{V}$	0.45		0.75	V
I_{CBO}	Collector Cutoff Current	$V_{CB}= 160\text{V}$; $I_E= 0$			10	μA
h_{FE}	DC Current Gain	$I_C= 200\text{mA}$; $V_{CE}= 5\text{V}$	60		320	
f_T	Current-Gain—Bandwidth Product	$I_C= 200\text{mA}$; $V_{CE}= 5\text{V}$		20		MHz